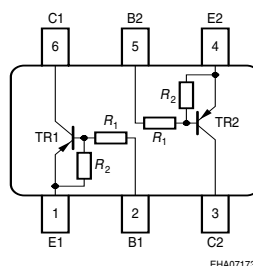
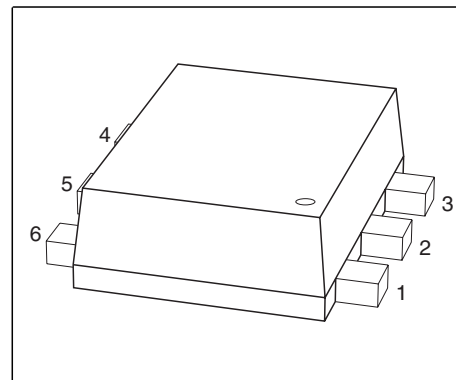


PNP Silicon Digital Transistor

Preliminary data

- Switching circuit, inverter, interface circuit, driver circuit
- Two (galvanic) internal isolated Transistors with good matching in one package
- Built in bias resistor ($R_1 = 4.7k\Omega$)



Type	Marking	Pin Configuration						Package
SEMB3	WS	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT666

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	50	V
Collector-base voltage	V_{CBO}	50	
Emitter-base voltage	V_{EBO}	5	
Input on Voltage	$V_{i(on)}$	15	
DC collector current	I_C	100	mA
Total power dissipation, $T_S = 75^\circ\text{C}$	P_{tot}	250	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

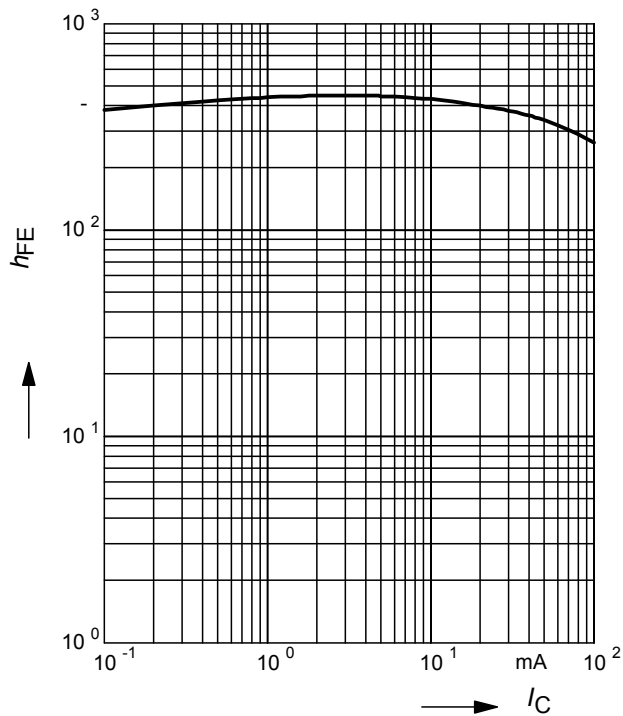
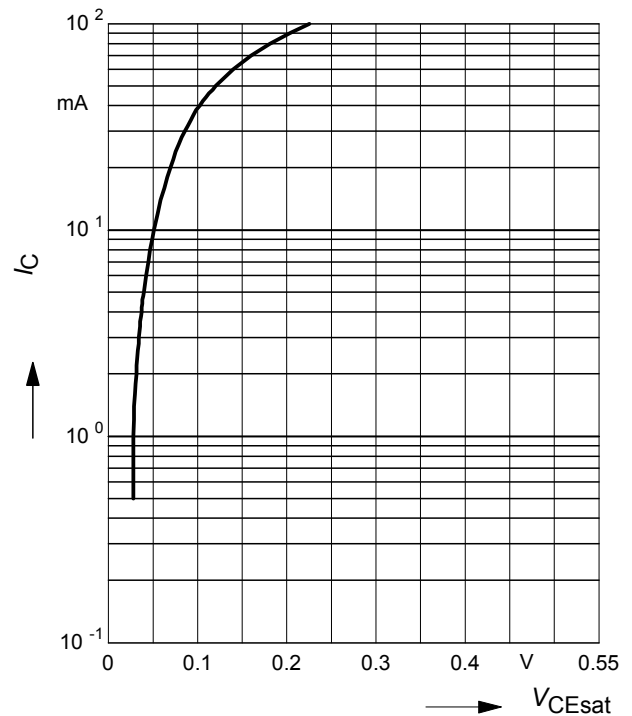
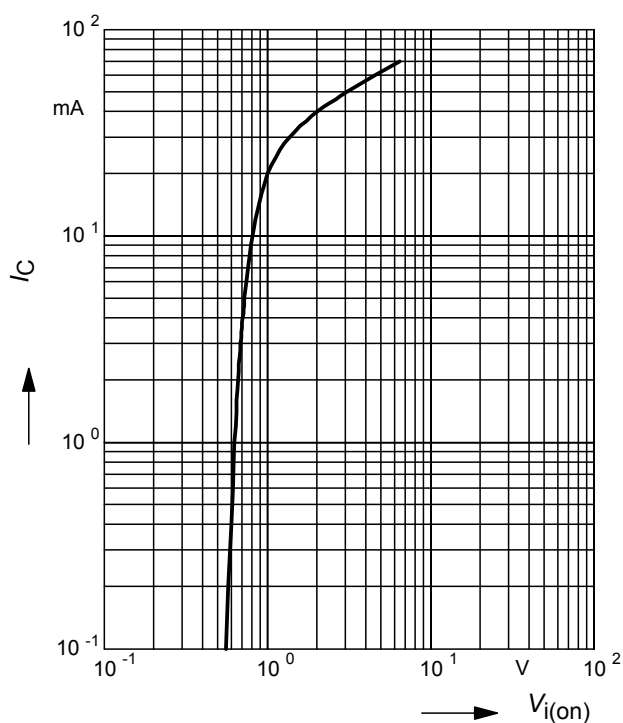
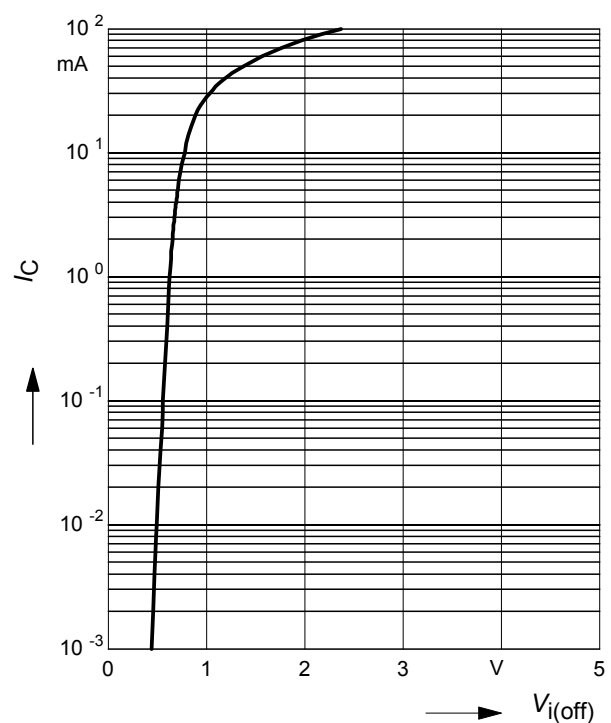
Junction - soldering point ¹⁾	R_{thJS}	≤ 300	K/W
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¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

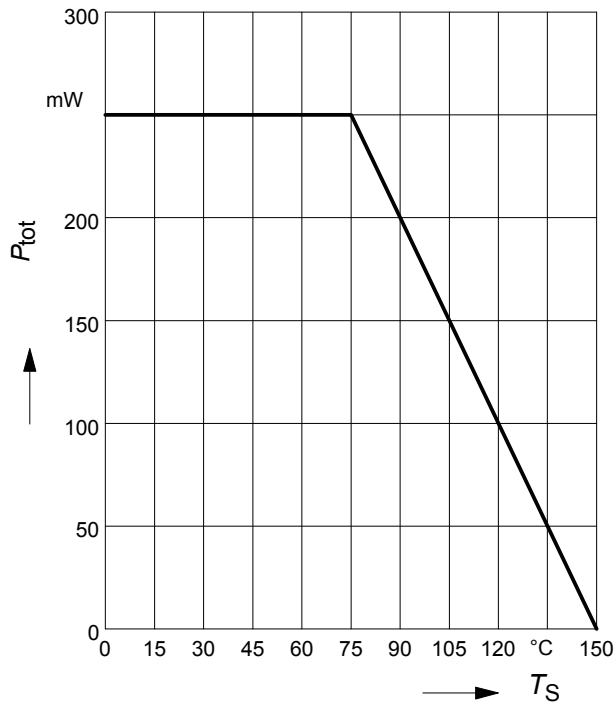
Electrical Characteristics at $T_A=25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 100\ \mu\text{A}$, $I_B = 0$	$V_{(\text{BR})\text{CEO}}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10\ \mu\text{A}$, $I_E = 0$	$V_{(\text{BR})\text{CBO}}$	50	-	-	
Emitter-base breakdown voltage $I_E = 10\ \mu\text{A}$, $I_C = 0$	$V_{(\text{BR})\text{EBO}}$	5	-	-	
Collector cutoff current $V_{\text{CB}} = 40\ \text{V}$, $I_E = 0$	I_{CBO}	-	-	100	nA
DC current gain 1) $I_C = 5\ \text{mA}$, $V_{\text{CE}} = 5\ \text{V}$	h_{FE}	120	-	630	-
Collector-emitter saturation voltage1) $I_C = 10\ \text{mA}$, $I_B = 0.5\ \text{mA}$	V_{CEsat}	-	-	0.3	V
Input off voltage $I_C = 100\ \mu\text{A}$, $V_{\text{CE}} = 5\ \text{V}$	$V_{\text{i(off)}}$	0.4	-	0.8	
Input on Voltage $I_C = 2\ \text{mA}$, $V_{\text{CE}} = 0.3\ \text{V}$	$V_{\text{i(on)}}$	0.5	-	1.1	
Input resistor	R_1	3.2	4.7	6.2	kΩ
AC Characteristics					
Transition frequency $I_C = 10\ \text{mA}$, $V_{\text{CE}} = 5\ \text{V}$, $f = 100\ \text{MHz}$	f_{T}	-	200	-	MHz
Collector-base capacitance $V_{\text{CB}} = 10\ \text{V}$, $f = 1\ \text{MHz}$	C_{cb}	-	3	-	pF

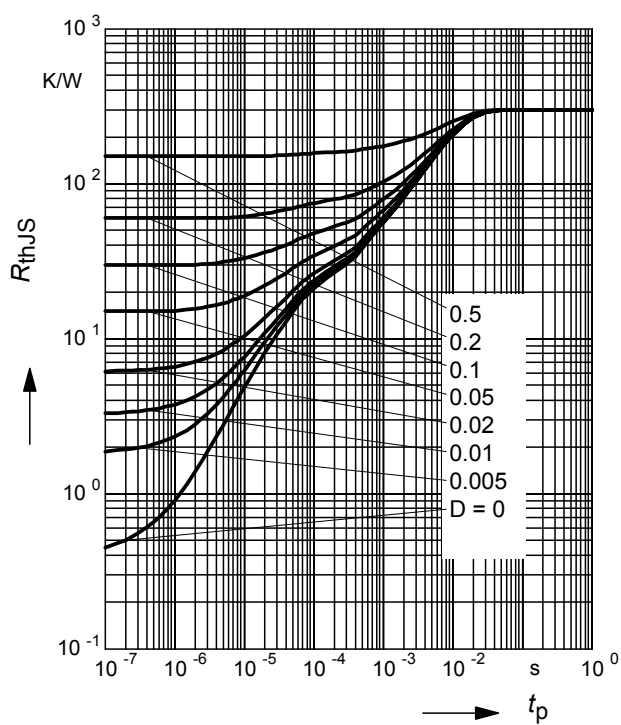
1) Pulse test: $t < 300\ \mu\text{s}$; $D < 2\%$

DC Current Gain $h_{FE} = f(I_C)$
 $V_{CE} = 5V$ (common emitter configuration)

Collector-Emitter Saturation Voltage
 $V_{CEsat} = f(I_C), h_{FE} = 20$

Input on Voltage $V_{i(on)} = f(I_C)$
 $V_{CE} = 0.3V$ (common emitter configuration)

Input off voltage $V_{i(off)} = f(I_C)$
 $V_{CE} = 5V$ (common emitter configuration)


Total power dissipation $P_{\text{tot}} = f(T_S)$



Permissible Pulse Load $R_{\text{thJS}} = f(t_p)$



Permissible Pulse Load

$P_{\text{totmax}} / P_{\text{totDC}} = f(t_p)$

